

# Thomas Walther

## List of Publications by Citations

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146  
papers

2,046  
citations

22  
h-index

41  
g-index

159  
ext. papers

2,167  
ext. citations

1.8  
avg, IF

4.69  
L-index

#	Paper	IF	Citations
146	Structural and doping effects in the half-metallic double perovskite A <sub>2</sub> CrWO <sub>6</sub> (A=Sr, Ba, and Ca). <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	290
145	Nature of the Stranski-Krastanow transition during epitaxy of InGaAs on GaAs. <i>Physical Review Letters</i> , <b>2001</b> , 86, 2381-4	7.4	220
144	Coexistence of clusters, GPB zones, S <sub>2</sub> -, S <sub>1</sub> - and S-phases in an Al <sub>0.9%</sub> Cu <sub>0.4%</sub> Mg alloy. <i>Acta Materialia</i> , <b>2000</b> , 48, 2751-2764	8.4	134
143	Stranski-Krastanow transition and epitaxial island growth. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	109
142	Laser-assisted synthesis of Au-Ag alloy nanoparticles in solution. <i>Journal of Physical Chemistry B</i> , <b>2006</b> , 110, 2549-54	3.4	92
141	Observation of vertical and lateral Ge segregation in thin undulating SiGe layers on Si by electron energy-loss spectroscopy. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 809-811	3.4	82
140	Structure and Chemistry of Basal-Plane Inversion Boundaries in Antimony Oxide-Doped Zinc Oxide. <i>Journal of the American Ceramic Society</i> , <b>2001</b> , 84, 2657-2668	3.8	68
139	A new experimental procedure to quantify annular dark field images in scanning transmission electron microscopy. <i>Journal of Microscopy</i> , <b>2006</b> , 221, 137-44	1.9	43
138	A quantitative study of compositional profiles of chemical vapour-deposited strained silicon/germanium/silicon layers by transmission electron microscopy. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 113-128	1.6	41
137	Combinatorial investigation of the isolated nanoparticle to coalescent layer transition in a gradient sputtered gold nanoparticle layer on top of polystyrene. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 021910	3.4	40
136	1.55 eV InAs quantum dots grown on a GaAs substrate using a GaAsSb metamorphic buffer layer. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 111906	3.4	35
135	Photofragmentation of phase-transferred gold nanoparticles by intense pulsed laser light. <i>Journal of Physical Chemistry B</i> , <b>2005</b> , 109, 15735-40	3.4	35
134	Electron energy-loss spectroscopic profiling of thin film structures: 0.39 nm line resolution and 0.04 eV precision measurement of near-edge structure shifts at interfaces. <i>Ultramicroscopy</i> , <b>2003</b> , 96, 401-11	3.1	35
133	Influence of intense pulsed laser irradiation on optical and morphological properties of gold nanoparticle aggregates produced by surface acid-base reactions. <i>Langmuir</i> , <b>2005</b> , 21, 4249-53	4	35
132	Defects, strain relaxation, and compositional grading in high indium content InGaN epilayers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 155301	2.5	34
131	Homogeneous array of nanowire-embedded quantum light emitters. <i>Nano Letters</i> , <b>2013</b> , 13, 861-5	11.5	33
130	A Correlation between Compositional Fluctuations and Surface Undulations in Strained Layer Epitaxy. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 505-510	0.4	30

129	First experimental test of a new monochromated and aberration-corrected 200 kV field-emission scanning transmission electron microscope. <i>Ultramicroscopy</i> , <b>2006</b> , 106, 963-9	3.1	27
128	Diffusion and segregation effects in doped manganite/titanate heterostructures. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3882-3884	3.4	25
127	A New Method to Measure Small Amounts of Solute Atoms on Planar Defects and Application to Inversion Domain Boundaries in Doped Zinc Oxide. <i>Journal of Materials Science</i> , <b>2004</b> , 12, 267-275		24
126	Quantification of carbon contamination under electron beam irradiation in a scanning transmission electron microscope and its suppression by plasma cleaning. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012017	0.3	23
125	Development of a new analytical electron microscopy technique to quantify the chemistry of planar defects and to measure accurately solute segregation to grain boundaries. <i>Journal of Microscopy</i> , <b>2004</b> , 215, 191-202	1.9	22
124	Microstructure and magnetoresistance of epitaxial films of the layered perovskite $\text{La}_{2-x}\text{Sr}_{1+2x}\text{Mn}_2\text{O}_7$ ( $x=0.3$ and $0.4$ ). <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	20
123	Influence of thick crystal effects on ptychographic image reconstruction with moveable illumination. <i>Ultramicroscopy</i> , <b>2009</b> , 109, 1263-75	3.1	19
122	Diffusion and Surface Segregation in Thin SiGe/Si Layers Studied by Scanning Transmission Electron Microscopy. <i>Defect and Diffusion Forum</i> , <b>1997</b> , 143-147, 1135-1140	0.7	19
121	Preliminary results from the first monochromated and aberration corrected 200-kV field-emission scanning transmission electron microscope. <i>Microscopy and Microanalysis</i> , <b>2006</b> , 12, 498-505	0.5	19
120	Epitaxial growth of relaxed germanium layers by reduced pressure chemical vapour deposition on (110) and (111) silicon substrates. <i>Thin Solid Films</i> , <b>2012</b> , 520, 3222-3226	2.2	18
119	High ultimate tensile stress in nano-grained superelastic NiTi thin films. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , <b>2006</b> , 415, 304-308	5.3	17
118	Quantitative microstructural and spectroscopic investigation of inversion domain boundaries in sintered zinc oxide ceramics doped with iron oxide. <i>International Journal of Materials Research</i> , <b>2006</b> , 97, 934-942	0.5	16
117	Quantitative characterization of AlAs/GaAs interfaces by high-resolution transmission electron microscopy along the <100> and the <110> projection. <i>Applied Physics A: Solids and Surfaces</i> , <b>1993</b> , 57, 393-400		15
116	Lattice resolved annular dark-field scanning transmission electron microscopy of (Al, In)GaN/GaN layers for measuring segregation with sub-monolayer precision. <i>Journal of Materials Science</i> , <b>2013</b> , 48, 2883-2892	4.3	14
115	Twin Boundaries in Zinc Oxide with Additions of Gallium Oxide. <i>Journal of Materials Science</i> , <b>2004</b> , 12, 213-226		14
114	Self-consistent method for quantifying indium content from X-ray spectra of thick compound semiconductor specimens in a transmission electron microscope. <i>Journal of Microscopy</i> , <b>2016</b> , 262, 151-6 <sup>1.9</sup>		13
113	Study of phase separation in an InGaN alloy by electron energy loss spectroscopy in an aberration corrected monochromated scanning transmission electron microscope. <i>Journal of Materials Research</i> , <b>2017</b> , 32, 983-995	2.5	10
112	Characterization of InGaN/GaN epitaxial layers by aberration corrected TEM/STEM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 546-549		10

111	Probe position recovery for ptychographical imaging. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012004	0.3	10
110	Linear least-squares fit evaluation of series of analytical spectra from planar defects: extension and possible implementations in scanning transmission electron microscopy. <i>Journal of Microscopy</i> , <b>2006</b> , 223, 165-70	1.9	10
109	Concentration quenching of the luminescence from trivalent thulium, terbium, and erbium ions embedded in an AlN matrix. <i>Journal of Luminescence</i> , <b>2014</b> , 145, 855-858	3.8	9
108	Similarity of Stranski-Krastanow growth of Ge/Si and SiGe/Si (001). <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 012003	2.5	9
107	Room-Temperature GaAs/AlGaAs Quantum Cascade Lasers Grown by Metal-Organic Vapor Phase Epitaxy. <i>IEEE Photonics Technology Letters</i> , <b>2011</b> , 23, 774-776	2.2	9
106	A Novel Method of Analytical Transmission Electron Microscopy for Measuring Highly Accurately Segregation to Special Grain Boundaries or Planar Interfaces. <i>Mikrochimica Acta</i> , <b>2006</b> , 155, 313-318	5.8	9
105	Critical assessment of the speckle statistics in fluctuation electron microscopy and comparison to electron diffraction. <i>Ultramicroscopy</i> , <b>2005</b> , 104, 206-19	3.1	9
104	Detection of random alloy fluctuations in high-resolution transmission electron micrographs of AlGaAs. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , <b>1995</b> , 72, 1015-1030		9
103	High Repetition Rate Ti:Sapphire Laser Mode-Locked by InP Quantum-Dot Saturable Absorber. <i>IEEE Photonics Technology Letters</i> , <b>2011</b> , 23, 1603-1605	2.2	8
102	Structural and magnetic characteristics of FeCo thin films modified by combinatorial ion implantation. <i>Thin Solid Films</i> , <b>2006</b> , 495, 169-174	2.2	8
101	A Study of Sulphur Diffusion in ZnMgSSe/ZnSe Quantum Wells by Energy-Loss Imaging in a Transmission Electron Microscope. <i>Physica Status Solidi A</i> , <b>2000</b> , 180, 351-356		8
100	How to best measure atomic segregation to grain boundaries by analytical transmission electron microscopy. <i>Journal of Materials Science</i> , <b>2014</b> , 49, 3898-3908	4.3	7
99	Structure of PtFe/Fe double-period multilayers investigated by X-ray diffraction, reflectivity, diffuse scattering and TEM. <i>Applied Surface Science</i> , <b>2006</b> , 253, 128-132	6.7	7
98	Fluctuation Electron Microscopy on a-Ge and Polycrystalline Gold. <i>Microscopy and Microanalysis</i> , <b>2003</b> , 9, 152-153	0.5	7
97	Auger depth profile analysis and EFTEM analysis of annealed Ti/Al-contacts on Si-doped GaN. <i>Applied Surface Science</i> , <b>2001</b> , 179, 213-221	6.7	7
96	Changes of the local oxygen content and ordering at twin boundaries of high-Tc YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> superconductors. <i>Physical Review B</i> , <b>1996</b> , 54, 16234-16237	3.3	7
95	Transmission electron microscopy of AlGaAs/GaAs quantum cascade laser structures. <i>Journal of Microscopy</i> , <b>2017</b> , 268, 298-304	1.9	6
94	Scanning transmission electron microscopy measurement of bismuth segregation in thin Ga(As,Bi) layers grown by molecular beam epitaxy. <i>Crystal Research and Technology</i> , <b>2015</b> , 50, 38-42	1.3	6

93	Electron microscopy of quantum dots. <i>Journal of Microscopy</i> , <b>2015</b> , 257, 171-8	1.9	6
92	Measurement of the Al content in AlGa <sub>N</sub> epitaxial layers by combined energy-dispersive X-ray and electron energy-loss spectroscopy in a transmission electron microscope. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 1079-1082		6
91	Nanoscale EELS analysis of elemental distribution and band-gap properties in AlGa <sub>N</sub> epitaxial layers. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012039	0.3	6
90	Study of annealed InAs/GaAs quantum dot structures. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012036	0.3	6
89	An improved approach to quantitative X-ray microanalysis in (S)TEM: Thickness dependentk-factors. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012016	0.3	6
88	GaN, AlGa <sub>N</sub> , HfO <sub>2</sub> based radial heterostructure nanowires. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012011	0.3	6
87	Comparison of experimental and theoretical X-ray intensities from (In)GaAs specimens investigated by energy-dispersive X-ray spectroscopy in a transmission electron microscope. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012029	0.3	6
86	The Stranski-Rastanow transition in SiGe epitaxy investigated by scanning transmission electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 187-190	1.6	5
85	New pathways for improved quantification of energy-dispersive X-ray spectra of semiconductors with multiple X-ray lines from thin foils investigated in transmission electron microscopy. <i>Journal of Microscopy</i> , <b>2015</b> , 260, 427-41	1.9	5
84	Combination of electron energy-loss spectroscopy and energy dispersive x-ray spectroscopy to determine indium concentration in InGa <sub>N</sub> thin film structures. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 114011	1.8	5
83	Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 114012	1.8	5
82	Calibration of thickness-dependentk-factors for germanium X-ray lines to improve energy-dispersive X-ray spectroscopy of SiGe layers in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012031	0.3	5
81	A simple method to improve the quantification accuracy of energy-dispersive X-ray microanalysis. <i>Journal of Physics: Conference Series</i> , <b>2008</b> , 126, 012090	0.3	5
80	Application of quantitative analytical electron microscopy to the mineral content of insect cuticle. <i>Microscopy and Microanalysis</i> , <b>2003</b> , 9, 152-4	0.5	5
79	Behavior of basic refractories at high temperatures in steelmaking processes thermodynamics and implications for the usability of olivine as refractory material. <i>European Journal of Mineralogy</i> , <b>2003</b> , 15, 193-205	2.2	5
78	Automated background subtraction technique for electron energy-loss spectroscopy and application to semiconductor heterostructures. <i>Journal of Microscopy</i> , <b>2016</b> , 262, 157-66	1.9	5
77	Aberration Corrected High-Resolution Transmission and Scanning Transmission Electron Microscopy of Thin Perovskite Layers. <i>Physics Procedia</i> , <b>2013</b> , 40, 49-55		4
76	Comparison of cross-sectional transmission electron microscope studies of thin germanium epilayers grown on differently oriented silicon wafers. <i>Journal of Microscopy</i> , <b>2017</b> , 268, 288-297	1.9	4

75	Transmission Electron Microscopy of Nanostructures <b>2017</b> , 105-134		4
74	Towards the structure of rare earth luminescence centres in terbium doped aluminium nitride as an example system. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012032	0.3	4
73	Comparison of the contrast in conventional and lattice resolved ADF STEM images of InGaAs/GaAs structures using different camera lengths. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012041	0.3	4
72	Direct observation by transmission electron microscopy of the influence of Ni catalyst-seeds on the growth of GaN/AlGaIn axial heterostructure nanowires. <i>Journal of Crystal Growth</i> , <b>2011</b> , 327, 27-34	1.6	4
71	Configuring a 300kV cold field-emission gun for optimum analytical performance. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 371, 012012	0.3	4
70	Quantitative investigation of the onset of islanding in strained layer epitaxy of InAs/GaAs by X-ray mapping in STEM. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012035	0.3	4
69	Atomic structure of basal-plane inversion boundaries in SnO <sub>2</sub> -doped ZnO. <i>Microscopy and Microanalysis</i> , <b>2003</b> , 9, 286-287	0.5	4
68	Evidence of terbium and oxygen co-segregation in annealed AlN:Tb. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 222102	3.4	4
67	Effective absorption correction for energy dispersive X-ray mapping in a scanning transmission electron microscope: analysing the local indium distribution in rough samples of InGaIn alloy layers. <i>Journal of Microscopy</i> , <b>2017</b> , 268, 248-253	1.9	3
66	Measurement of Diffusion and Segregation in Semiconductor Quantum Dots and Quantum Wells by Transmission Electron Microscopy: A Guide. <i>Nanomaterials</i> , <b>2019</b> , 9,	5.4	3
65	What environmental transmission electron microscopy measures and how this links to diffusivity: thermodynamics versus kinetics. <i>Journal of Microscopy</i> , <b>2015</b> , 257, 87-91	1.9	3
64	Twinning in GaAs nanowires on patterned GaAs(111)B. <i>Crystal Research and Technology</i> , <b>2015</b> , 50, 62-68	1.3	3
63	Stranski-Krastanov growth of (Si)Ge/Si(001): transmission electron microscopy compared with segregation theory. <i>Materials Science and Technology</i> , <b>2018</b> , 34, 1539-1548	1.5	3
62	Self-consistent absorption correction for quantifying very noisy X-ray maps: group III nitride nanowires as an example. <i>Journal of Microscopy</i> , <b>2018</b> , 272, 111-122	1.9	3
61	Self-consistent absorption correction for quantitative energy- dispersive X-ray spectroscopy of InGaIn layers in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2015</b> , 644, 012006	0.3	3
60	Accurate measurement of atomic segregation to grain boundaries or to planar faults by analytical transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 310-313		3
59	Study of site controlled quantum dot formation on focused ion beam patterned GaAs substrate. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012047	0.3	3
58	GaAsBi atomic surface order and interfacial roughness observed by STM and TEM. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012060	0.3	3

57	Measuring the contrast in annular dark field STEM images as a function of camera length. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012068	0.3	3
56	A comparison of transmission electron microscopy methods to measure wetting layer thicknesses to sub-monolayer precision. <i>Journal of Physics: Conference Series</i> , <b>2008</b> , 126, 012091	0.3	3
55	Thermal Stability of ZnMgSSe/ZnSe Laser Heterostructures. <i>Physica Status Solidi A</i> , <b>2001</b> , 185, 301-308		3
54	Stripe TEM as a method of calculating chemical profiles across interfaces between solids or core-shell structures using electron energy-loss spectroscopic profiling. <i>International Journal of Materials Research</i> , <b>2005</b> , 96, 429-437		3
53	Investigation of phase separation in InGaN alloys by plasmon loss spectroscopy in a TEM. <i>MRS Advances</i> , <b>2016</b> , 1, 2749-2756	0.7	3
52	ConceptEM: a new method to quantify solute segregation to interfaces or planar defect structures by analytical TEM and applications to inversion domain boundaries in doped zinc oxide <b>2005</b> , 199-202		3
51	Investigating the Capping of InAs Quantum Dots by InGaAs. <i>Springer Proceedings in Physics</i> , <b>2008</b> , 259-262	2	3
50	Microscopy of Semiconducting Materials 2015. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 110301	1.8	2
49	Accurate calibration for the quantification of the Al content in AlGaInP epitaxial layers by energy-dispersive X-ray spectroscopy in a Transmission Electron Microscope. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012028	0.3	2
48	High temperature ~4 [micro sign]m In <sub>0.7</sub> Ga <sub>0.3</sub> As/In <sub>0.34</sub> Al <sub>0.66</sub> As quantum cascade lasers grown by MOVPE. <i>Electronics Letters</i> , <b>2011</b> , 47, 559	1.1	2
47	Study of the effect of annealing of In(Ga)As quantum dots. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012054	0.3	2
46	STEM imaging of InP/AlGaInP quantum dots. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012087	0.3	2
45	Transmission electron microscopy study of Si Doped GaAs/AlGaAs/InGaAs/GaAs pseudomorphic high electron mobility transistor structures. <i>Thin Solid Films</i> , <b>1997</b> , 307, 6-9	2.2	2
44	Measurement of diffusion lengths in quaternary semiconducting thin layers by spectrum imaging. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 1161-1164	2.8	2
43	Diffusion Processes in Strained Silicon Germanium Island Structures. <i>Defect and Diffusion Forum</i> , <b>2000</b> , 183-185, 53-60	0.7	2
42	The Scattering Distribution from Semiconductors as a Function of Angle and Energy Loss in the Electron Microscope. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 466, 113		2
41	17th International Conference on Microscopy of Semiconducting Materials 2011. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 011001	0.3	2
40	TEM Characterization of ZnO Nanorods. <i>Springer Proceedings in Physics</i> , <b>2008</b> , 247-250	0.2	2

39	X-ray mapping in a scanning transmission electron microscope of InGaAs quantum dots with embedded fractional monolayers of aluminium. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 35, 084001 <sup>1.8</sup>	1.8	1
38	Comment on Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy <i>Nanotechnology</i> , <b>2018</b> , 29, 318001	3.4	1
37	Preface of 19(th) Microscopy of Semiconducting Materials conference. <i>Journal of Microscopy</i> , <b>2016</b> , 262, 131-3	1.9	1
36	GaN-based radial heterostructure nanowires grown by MBE and ALD. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012039	0.3	1
35	Investigation of boron implantation into silicon by quantitative energy-filtered transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012053	0.3	1
34	A TEM study of Ge-on-(111)Si structures for potential use in high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012023	0.3	1
33	Characterization of thickness, elemental distribution and band-gap properties in AlGaIn/GaN quantum wells by aberration-corrected TEM/STEM. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 371, 012014	0.3	1
32	Self-consistent absorption corrections for low-energy X-ray lines in energy-dispersive X-ray spectroscopy. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 371, 012063	0.3	1
31	Performance of a cold-field emission gun double aberration corrected TEM/STEM at 80kV. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 371, 012013	0.3	1
30	TEM analysis of Ge-on-Si MOSFET structures with HfO <sub>2</sub> dielectric for high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012061	0.3	1
29	Influence of pumping and inherent laser light on properties and degradation of ZnMgSSe/ZnSe quantum well heterostructures. <i>Physica Status Solidi A</i> , <b>2003</b> , 195, 188-193		1
28	Measurement of Oxygen Disorder and Nano-Twin Microstructure Associated with Columnar Defects in YBCO. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 540, 267		1
27	Preface to special issue on Microscopy of Semiconducting Materials 2017 (MSM-XX). <i>Journal of Microscopy</i> , <b>2017</b> , 268, 221-224	1.9	1
26	Structural and Compositional Properties of Strain-Symmetrized SiGe/Si Heterostructures. <i>Springer Proceedings in Physics</i> , <b>2008</b> , 269-272	0.2	1
25	Failure Analysis of Some Commercial Spotlights Based on Light Emitting Diodes. <i>Electronics (Switzerland)</i> , <b>2022</b> , 11, 48	2.6	1
24	Electro-Assisted Photo-Luminescence of Colloidal Germanium Nanoparticles. <i>Zeitschrift Fur Physikalische Chemie</i> , <b>2007</b> , 221, 377-386	3.1	0
23	The nature of islanding in the InGaAs / GaAs epitaxial system. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 648, 1		0
22	Measuring grain boundary segregation: tomographic atom probe field ion microscopy (APFIM) vs. analytical scanning transmission electron microscopy (STEM). <i>Journal of Physics: Conference Series</i> , <b>2019</b> , 1190, 012002	0.3	



21	The influence of emitter conditioning on the performance of a tungsten cold field emission gun operating at 300 kV. <i>Journal of Physics: Conference Series</i> , <b>2014</b> , 522, 012053	0.3
20	Controlled Quantum Dot Formation on Focused Ion Beam-Patterned GaAs Substrates. <i>Lecture Notes in Nanoscale Science and Technology</i> , <b>2013</b> , 299-314	0.3
19	Investigation of growth of thin layers of perovskite on native silicon dioxide by a combination of atomic force microscopy and transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012037	0.3
18	Analysis of partially oxidised epitaxial silicon mono-layers on germanium virtual substrates using aberration corrected scanning transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012050	0.3
17	Quantification of series of X-ray spectra taken at different tilts in analytical transmission electron microscopy. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012037	0.3
16	TEM analysis of Si-passivated Ge-on-Si MOSFET structures for high performance PMOS device technology. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012044	0.3
15	Electron microscopy of AlGaIn-based multilayers for UV laser devices. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 241, 012048	0.3
14	The Mechanism of the Stranski-Krastanov Transition <b>2005</b> , 71-88	
13	Strategies for investigating core-shell particles by energy-filtered transmission electron microscopy. <i>Microscopy and Microanalysis</i> , <b>2003</b> , 9, 98-99	0.5
12	Combinatorial Thin Film Synthesis of NiMnAl Magnetic Shape Memory Alloys Using MBE Technique. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 785, 231	
11	Epitaxial Island Growth and the Stranski-Krastanow Transition. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 696, 1	
10	Quantitative microstructural and spectroscopic investigation of inversion domain boundaries in sintered zinc oxide ceramics doped with iron oxide. <i>International Journal of Materials Research</i> , <b>2022</b> , 97, 934-942	0.5
9	Quantifying the Top-Bottom Effect in Energy-Dispersive X-Ray Spectroscopy of Nanostructures Embedded in Thin Films. <i>Springer Proceedings in Physics</i> , <b>2008</b> , 185-188	0.2
8	Comparison of monochromated electron energy-loss with X-ray absorption near-edge spectra: ELNES vs. XANES <b>2008</b> , 65-66	
7	Comparison of transmission electron microscopy methods to measure layer thicknesses to sub-monolayer precision <b>2008</b> , 377-378	
6	Preface for the special issue on Microscopy of Semiconducting Materials 2019. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 35, 120201	1.8
5	Correlating compositional, structural and optical properties of InGaIn quantum wells by transmission electron microscopy <b>2018</b> , 267-272	
4	Electron energy loss spectroscopic profiling of semiconductor hetero- and nano-structures: theory, implementation, applications <b>2018</b> , 27-32	

- 3 How InGaAs islands form on GaAs substrates: the missing link in the explanation of the Stranski-Krastanow transition **2018**, 85-88
- 2 Joint plasmon and core-loss fitting for electron energy loss spectroscopy of InGaN **2016**, 893-894
- 1 Influence of background subtraction and deconvolution on calculation of EELS core-loss intensities **2016**, 891-892